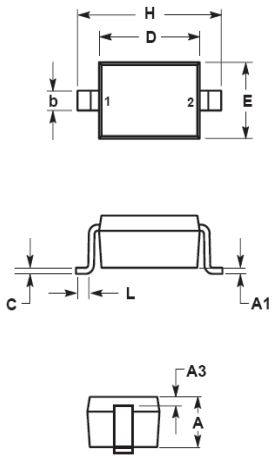
HAICHUANG SEMI

BZT52C2V0S~BZT52C75S

SURFACE MOUNT ZENMER DIODE

Features

- Total power dissipation: Max.200 mW.
- Low Zener Impedance.
- High Stability and High Reliability.



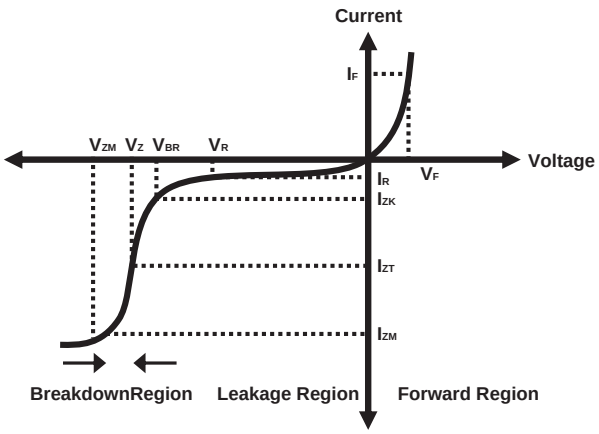
SOD-323		
Dim.	Min.	Max.
A	0.80	1.10
A1	0.00	0.10
A3	0.15 REF	
B	0.25	0.40
C	0.10	0.15
D	1.60	1.80
E	1.15	1.35
L	0.20	0.50
H	2.30	2.80
Dimensions in millimeter		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	- 65 to + 150	°C
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Forward Voltage at I_F = 10 mA	V_F	0.9	V

1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²
2) Short duration test pulse used to minimize self-heating effect
3) f=1KHz

Zener I vs. V Characteristics



V_{BR} : Voltage at I_{ZK}
I_{ZK} : Test current for voltage V_{BR}
Z_{ZK} : Dynamic impedance at I_{ZK}
I_{ZT} : Test current for voltage V_Z
V_Z : Voltage at current I_{ZT}
Z_{ZT} : Dynamic impedance at I_{ZT}
I_{ZM} : Maximum steady state current
V_{ZM} : Voltage at I_{ZM}

BZT52C2V0S~BZT52C75S

SURFACE MOUNT ZENMER DIODE

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Device	Marking	Zener Voltage Range				Maximum Zener Impedance 3)			Maximum Reverse Current		Typical Temperature coefficent @ IZTC=mV/℃		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR			
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V	Min	Max	mA
BZT52C2V0S	WY	2.0	1.80	2.15	5	150	600	1.0	100	1.0	-3.5	0	5
BZT52C2V4S	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7S	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0S	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3S	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6S	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9S	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3S	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7S	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1S	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6S	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2S	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8S	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5S	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2S	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1S	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10S	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11S	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12S	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13S	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15S	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16S	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18S	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20S	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22S	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24S	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27S	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30S	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33S	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36S	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39S	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43S	WU	43	40.0	46.0	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52C47S	WV	47	44.0	50.0	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52C51S	WW	51	48.0	54.0	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52C56S	XW	56	52.0	60.0	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52C62S	6E	62	58.0	66.0	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52C68S	6F	68	64.0	72.0	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52C75S	6H	75	70.0	79.0	2	300	1000	1.0	0.2	57	10.0	12.0	5

TYPICAL TRANSIENT CHARACTERISTICS

FIG 1 Typical Forward Characteristics

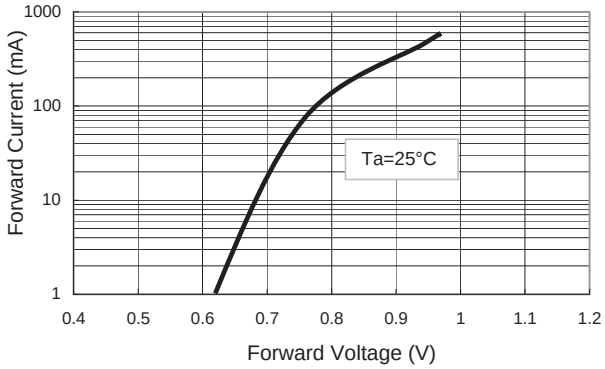


FIG 2 Zener Breakdown Characteristics

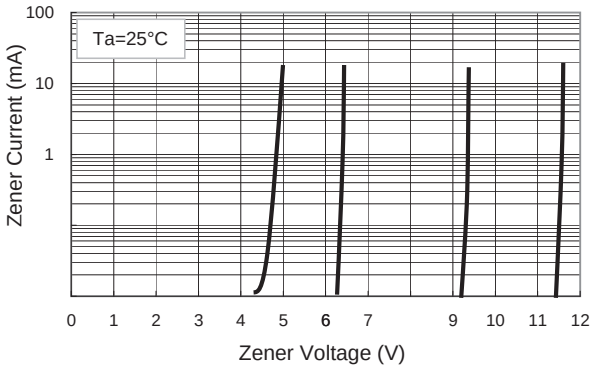


FIG 3 Zener Breakdown Characteristics

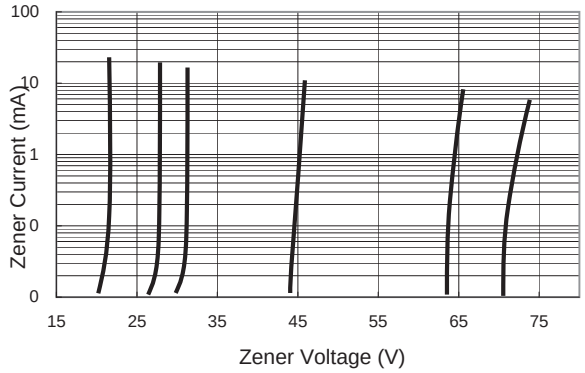


FIG 4 Admissible Power Disspation Curve

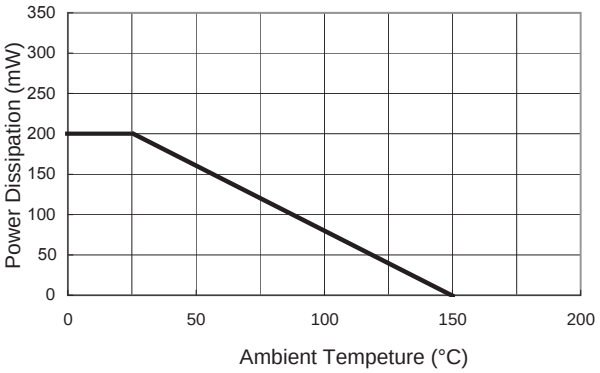


FIG 5 Typical Capacitance

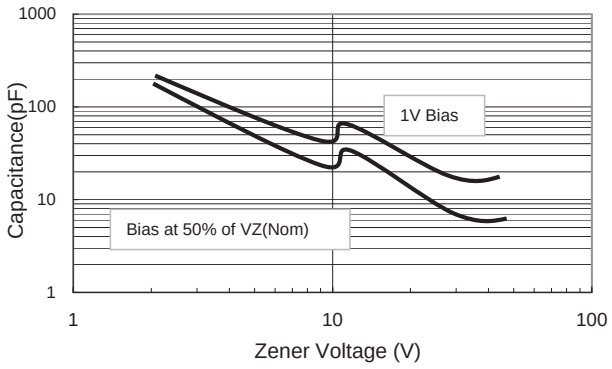
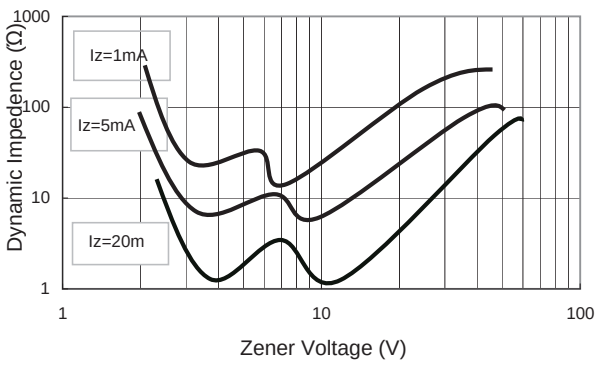


FIG 6 Effect of Zener Voltage on Impedence



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